

1. A nMOS transistor has the following parameters:  $V_{Tn} = +1\text{ V}$ ,  $k_n' = 1\text{ mA/V}^2$ ,  $\lambda = 0.01\text{ V}^{-1}$ ,  $V_{DD} = +10\text{ V}$ ,  $V_{SS} = 0\text{ V}$ .
  - I. Find out the DC biasing condition ( $V_{GG,n}$  and  $R_D$ ) such that  $I_{DS} = 4.5\text{ mA}$  and the transistor is in the saturation region assuming a) the effect of  $\lambda$  is negligible and b) taking into account the effect of  $\lambda$ .
  - II. Find out the CS gain of the above amplifier when output is taken from the drain terminal for both the above cases.
  - III. Find out the required value for  $V_{DD}$  such that the DC biasing condition is not changed with  $R_D = r_o$  without neglecting the effect of  $\lambda$ .
  - IV.  $R_D$  is now replaced with a p-MOS in saturation having the following device parameters:  $V_{Tp} = -1\text{ V}$ ,  $k_p' = 1/3\text{ mA/V}^2$ ,  $\lambda = 0.01\text{ V}^{-1}$  without changing the DC biasing condition for the nMOS. The resistance offered by the p-MOS is  $r_o$  as in III. Find out all the biasing voltages ( $V_{GG,n}$ ,  $V_{GG,p}$ ,  $V_{DD}$ , and  $V_{SS} = 0$ ) such that the DC biasing condition remains as in I a) neglecting the effect of  $\lambda$  and b) including the effect of  $\lambda$ .
  - V. Find out the CS gain of the amplifier in IV taking into account the effect of  $\lambda$ .
  - VI. Redesign the circuit in IV with non-zero  $V_{SS}$  such that the DC voltage at the drain node of nMOS is zero. Consider both the cases when a)  $\lambda$  is negligible and b)  $\lambda$  is not negligible.
  - VII. Redesign the circuit in IV with non-zero  $V_{SS}$  and  $R_S = 1\text{ k}\Omega$  such that the DC voltage at the drain node of nMOS is zero. Consider both the cases when a)  $\lambda$  is negligible and b)  $\lambda$  is not negligible.
  - VIII. Find out the CS gain of the amplifier in VII taking into account the effect of  $\lambda$ .
  - IX. Find out the CS gain of the amplifier in VII at 1 kHz, 1 MHz and 1 GHz when  $R_S$  is connected with a source bypass capacitor of 100 nF taking into account the effect of  $\lambda$ .